CSD25310Q2 20V P-Channel NexFET™ Power MOSFETs

1 Features

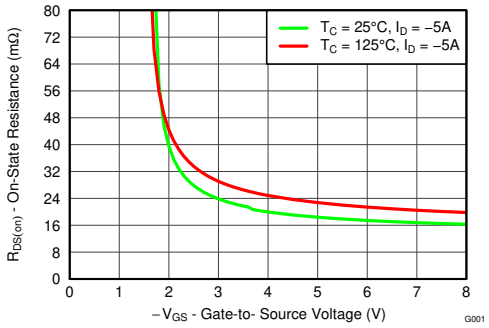
- Ultra-low Q_g and Q_{gd}
- Low on resistance
- Low thermal resistance
- Pb-free
- RoHS compliant
- Halogen free
- SON 2mm × 2mm plastic package

2 Applications

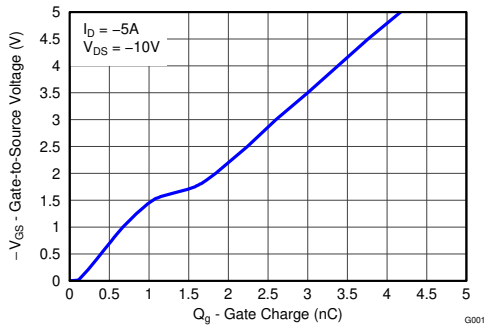
- Battery management
- Load management
- Battery protection

3 Description

This 19.9mΩ, –20V P-Channel device is designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra-low profile. Its low on resistance coupled with an extremely small footprint in a SON 2mm × 2mm plastic package make the device ideal for battery operated space constrained operations.



$R_{DS(on)}$ vs V_{GS}



Gate Charge

Product Summary

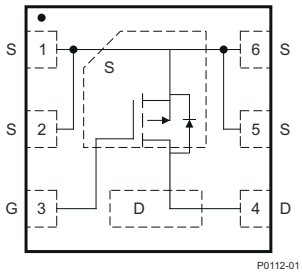
T_A = 25°C		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	–20		V
Q_g	Gate Charge Total (–4.5V)	3.6		nC
Q_{gd}	Gate Charge Gate to Drain	0.5		nC
$R_{DS(on)}$	Drain-to-Source On Resistance	V_{GS} = –1.8V	59.0	mΩ
		V_{GS} = –2.5V	27.0	mΩ
		V_{GS} = –4.5V	19.9	mΩ
$V_{GS(th)}$	Threshold Voltage	-0.85		V

Ordering Information

Device	Media	Qty	Package	Ship
CSD25310Q2	7-Inch Reel	3000	SON 2mm x 2mm Plastic Package	Tape and Reel
CSD25310Q2T	7-Inch Reel	250		

Absolute Maximum Ratings

T_A = 25°C		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	–20	V
V_{GS}	Gate-to-Source Voltage	±8	V
I_D	Continuous Drain Current (Package Limit)	–20	A
	Continuous Drain Current(1)	–9.6	A
I_{DM}	Pulsed Drain Current(2)	48	A
P_D	Power Dissipation 1. $R_{\theta JA}$ = 43°C/W on 1 in² Cu (2 oz.) on .060-inch thick FR4 PCB.	2.9	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	–55 to 150	°C



Top View

Table of Contents

4 Specifications

4.1 Electrical Characteristics

T_A = 25°C, unless otherwise specified

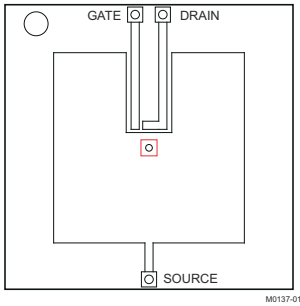
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0V, I_D = –250µA	–20			V
I_{DSS}	Drain-to-Source Leakage Current	V_{GS} = 0V, V_{DS} = –16V			–1	µA
I_{GSS}	Gate-to-Source Leakage Current	V_{DS} = 0V, V_{GS} = –8V			–100	nA
$V_{GS(th)}$	Gate-to-Source Threshold Voltage	V_{DS} = V_{GS}, I_{DS} = –250µA	–0.55	–0.85	–1.10	V
$R_{DS(on)}$	Drain-to-Source On Resistance	V_{GS} = –1.8V, I_{DS} = –5A		59.0	89.0	mΩ
		V_{GS} = –2.5V, I_{DS} = –5A		27.0	32.5	mΩ
		V_{GS} = –4.5V, I_{DS} = –5A		19.9	23.9	mΩ
g_{fs}	Transconductance	V_{DS} = –16V, I_{DS} = –5A		34		S
DYNAMIC CHARACTERISTICS						
C_{ISS}	Input Capacitance	V_{GS} = 0V, V_{DS} = –10V, f = 1MHz		504	655	pF
C_{OSS}	Output Capacitance			281	365	pF
C_{RSS}	Reverse Transfer Capacitance			16.7	21.7	pF
R_g	Series Gate Resistance			1.9		Ω
Q_g	Gate Charge Total (–4.5 V)	V_{DS} = –10V, I_{DS} = –5A		3.6	4.7	nC
Q_{gd}	Gate Charge Gate to Drain			0.5		nC
Q_{gs}	Gate Charge Gate to Source			1.1		nC
$Q_{g(th)}$	Gate Charge at V_{th}			0.6		nC
Q_{OSS}	Output Charge	V_{DS} = –10V, V_{GS} = 0V		5.0		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = –10V, V_{GS} = –4.5V, I_{DS} = –5A R_G = 2Ω		8		ns
t_r	Rise Time			15		ns
$t_{d(off)}$	Turn Off Delay Time			15		ns
t_f	Fall Time			5		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode Forward Voltage	I_{DS} = –5A, V_{GS} = 0V		–0.8	–1.0	V
Q_{rr}	Reverse Recovery Charge	V_{DD} = –10V, I_F = –5A, di/dt = 200A/µs		9.2		nC
t_{rr}	Reverse Recovery Time			13		ns

4.2 Thermal Information

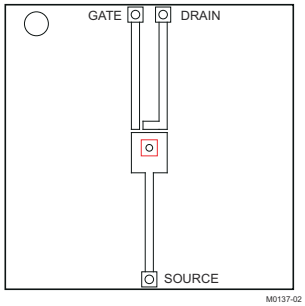
(T_A = 25°C unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case(1)			4.5	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient(1) (2)			55	

(1) $R_{\theta JC}$ is determined with the device mounted on a 1 inch^2 (6.45cm^2), 2oz. (0.071mm thick) Cu pad on a 1.5 inch × 1.5 inch (3.81cm × 3.81cm), 0.06 inch (1.52mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1 inch^2 (6.45cm^2), 2oz. (0.071mm thick) Cu.



Max $R_{\theta JA}$ = 55 when mounted on 1 inch^2 (6.45cm^2) of 2oz. (0.071mm thick) Cu.



Max $R_{\theta JA}$ = 215 when mounted on minimum pad area of 2oz. (0.071mm thick) Cu.

4.3 Typical MOSFET Characteristics

(T_A = 25°C unless otherwise stated)

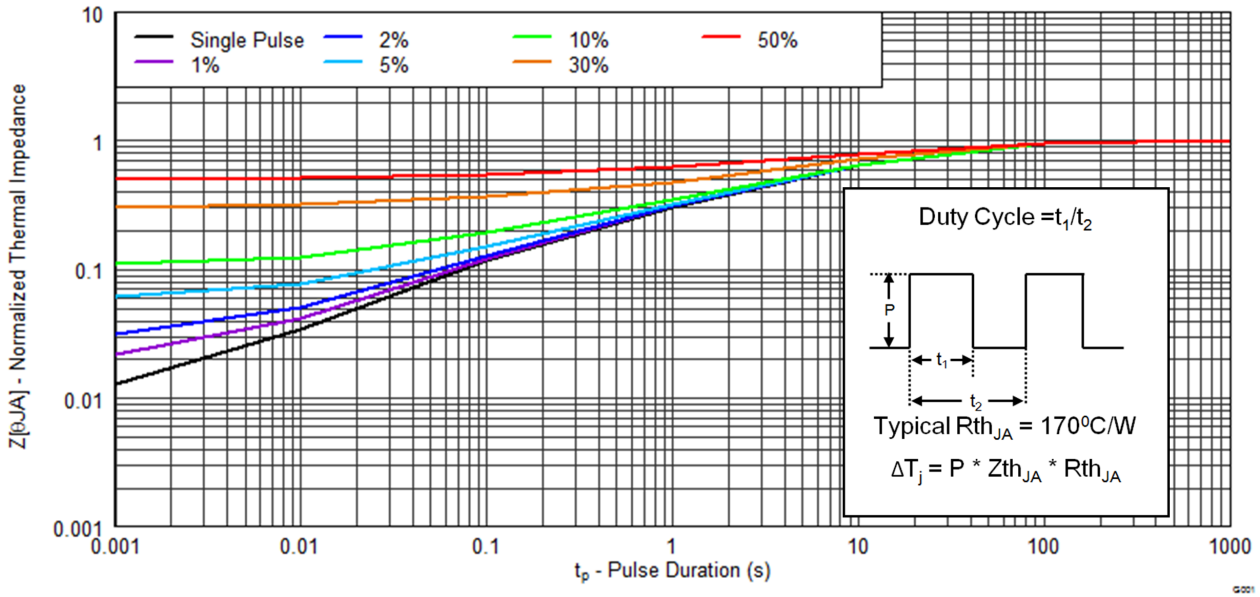


Figure 4-1. Transient Thermal Impedance

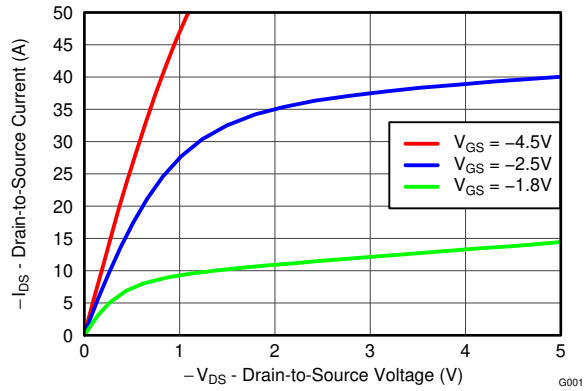


Figure 4-2. Saturation Characteristics

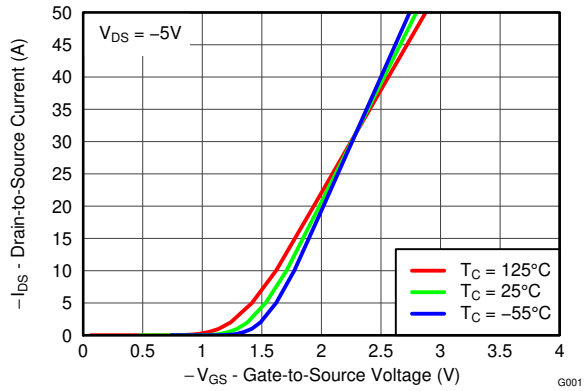


Figure 4-3. Transfer Characteristics

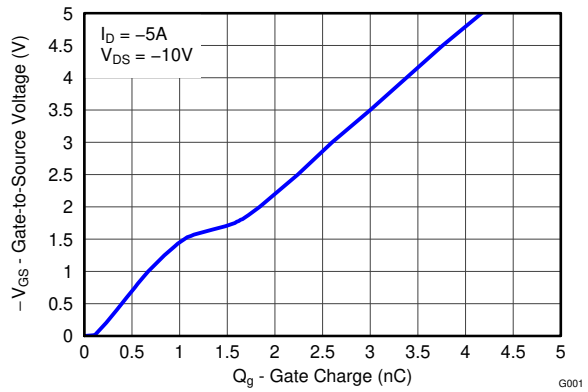


Figure 4-4. Gate Charge

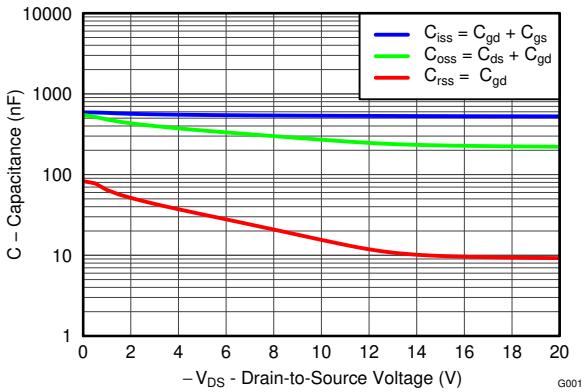


Figure 4-5. Capacitance

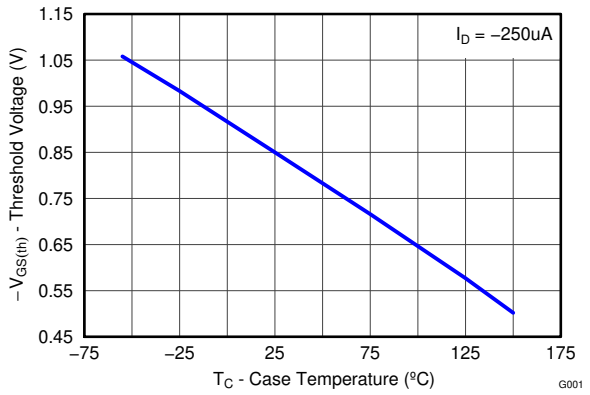


Figure 4-6. Threshold Voltage vs Temperature

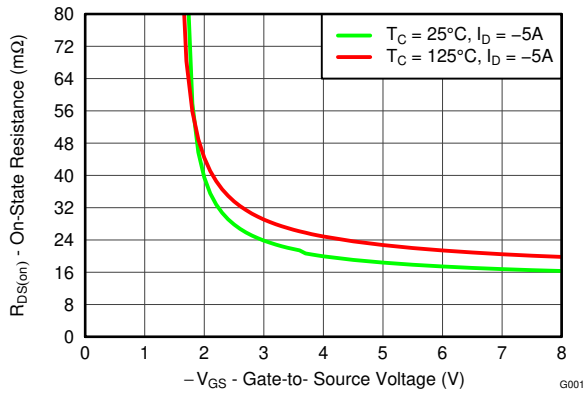


Figure 4-7. On-State Resistance vs Gate-to-Source Voltage

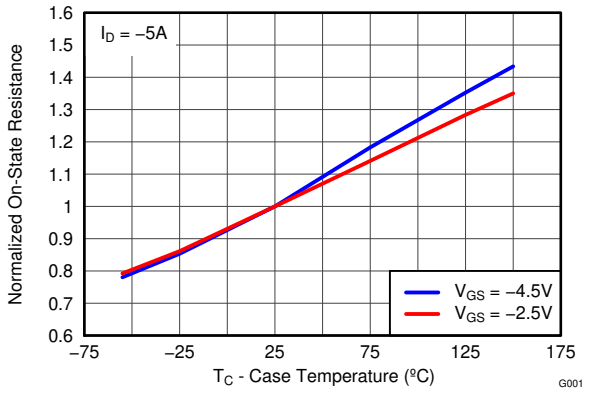


Figure 4-8. Normalized On-State Resistance vs Temperature

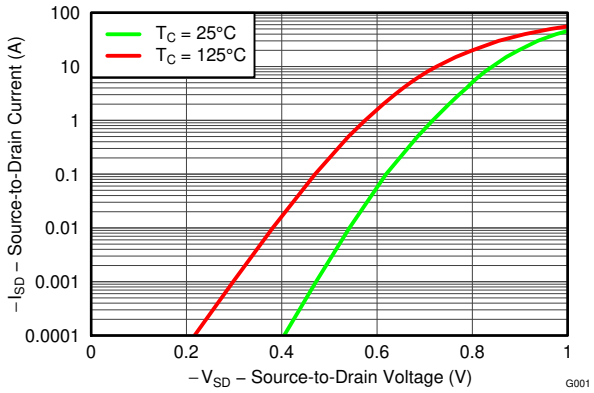


Figure 4-9. Typical Diode Forward Voltage

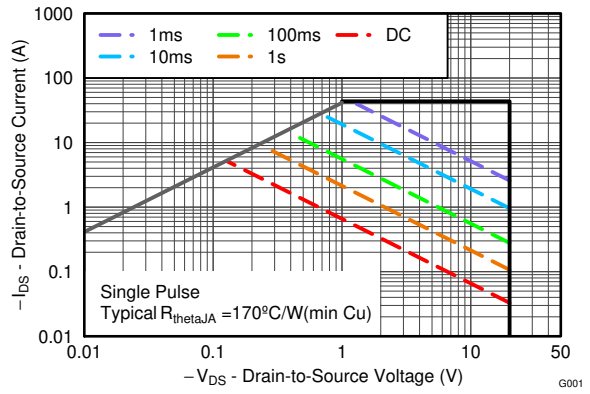


Figure 4-10. Maximum Safe Operating Area

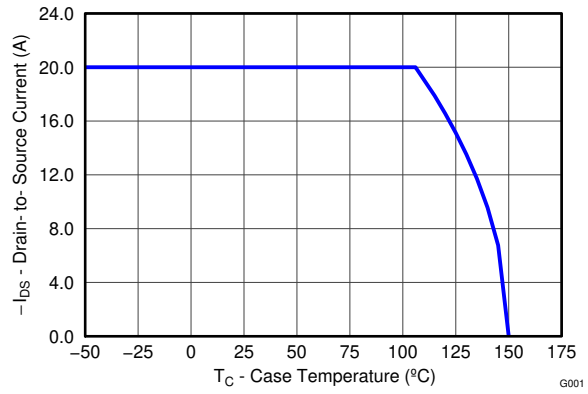


Figure 4-11. Maximum Drain Current vs Temperature

5 Device and Documentation Support

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5.2 Documentation Support

5.2.1 Related Documentation

5.3 Receiving Notification of Documentation Updates

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5.4 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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5.6 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

5.7 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

6 Revision History

Changes from Revision B (March 2022) to Revision C (February 2025)	Page
• Updated the numbering format for tables, figures, and cross-references throughout the document	1

Changes from Revision A (June 2014) to Revision B (March 2022)	Page
• Updated drain and source connection images	4

Changes from Revision * (January 2014) to Revision A (June 2014)	Page
• Revised "Pb-Free Terminal Plating" to Only State "Pb-Free"	1
• Added small reel option to the Ordering Information Table	1

7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD25310Q2	Active	Production	WSON (DQK) | 6	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	2530
CSD25310Q2.B	Active	Production	WSON (DQK) | 6	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	2530
CSD25310Q2G4.B	Active	Production	WSON (DQK) | 6	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	2530
CSD25310Q2T	Active	Production	WSON (DQK) | 6	250 | SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	2530
CSD25310Q2T.B	Active	Production	WSON (DQK) | 6	250 | SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	2530

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

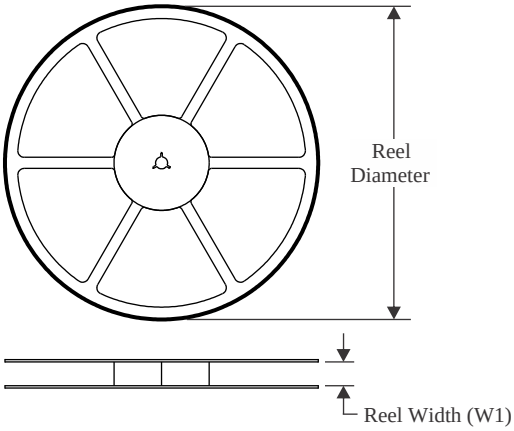
(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

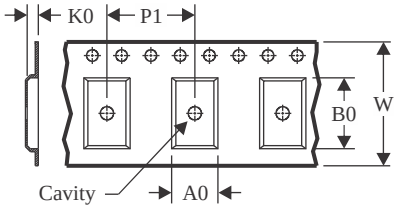
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

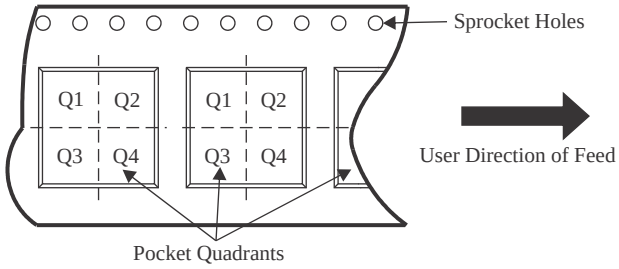


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

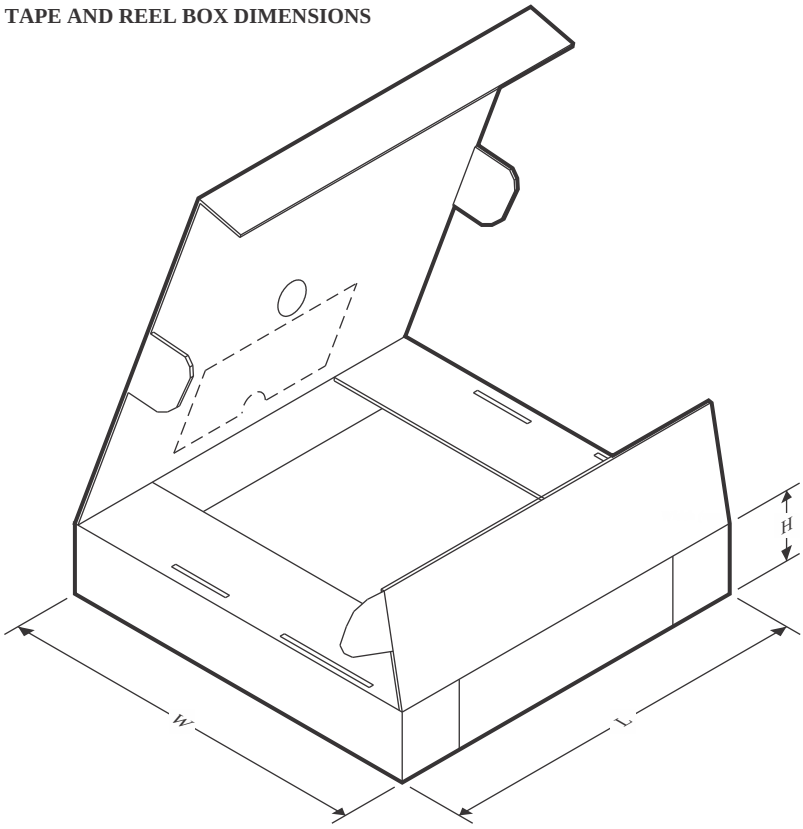
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD25310Q2	WSON	DQK	6	3000	180.0	9.5	2.3	2.3	1.0	4.0	8.0	Q1
CSD25310Q2T	WSON	DQK	6	250	180.0	9.5	2.3	2.3	1.0	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD25310Q2	WSON	DQK	6	3000	189.0	185.0	36.0
CSD25310Q2T	WSON	DQK	6	250	189.0	185.0	36.0

GENERIC PACKAGE VIEW

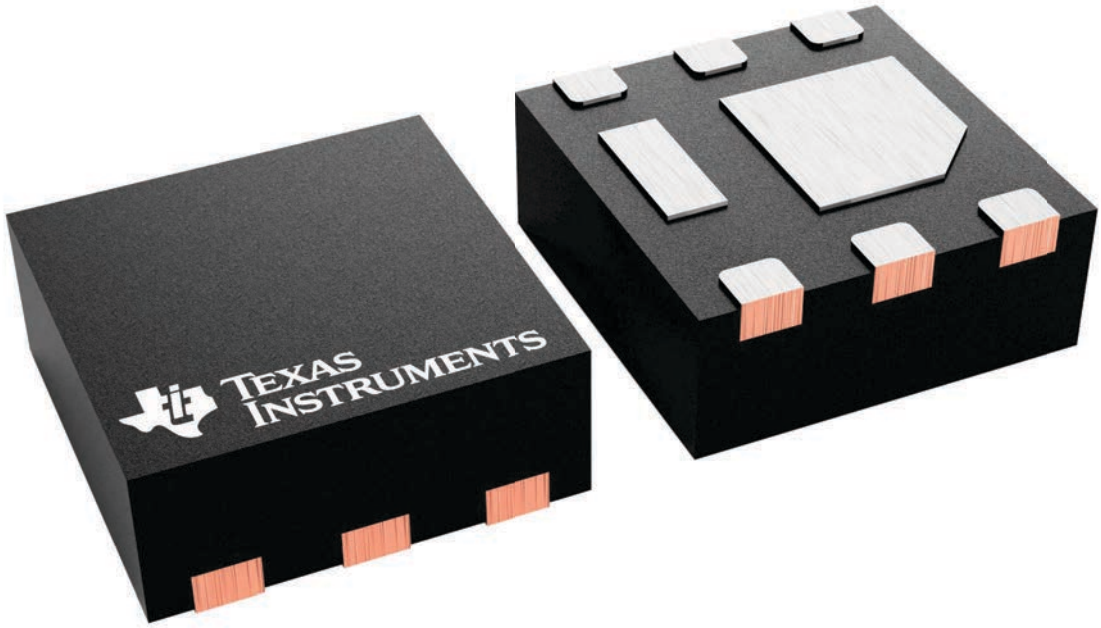
DQK 6

WSON - 0.8 mm max height

2 x 2, 0.65 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



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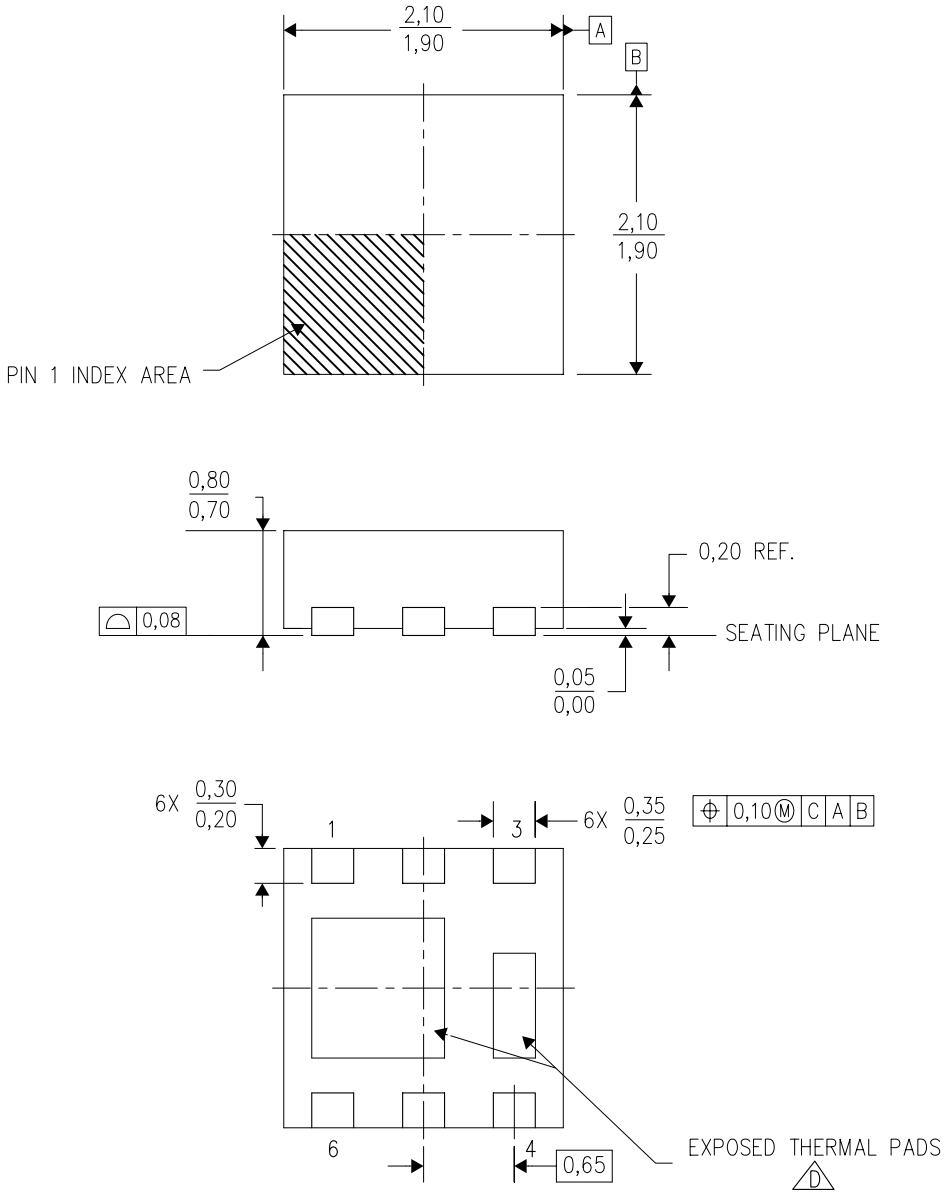
DQK (S–PWSON–N6) PLASTIC SMALL OUTLINE NO–LEAD



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NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Small Outline No–Lead (SON) package configuration.
D. The package thermal pads must be soldered to the board for thermal and mechanical performance.

THERMAL PAD MECHANICAL DATA

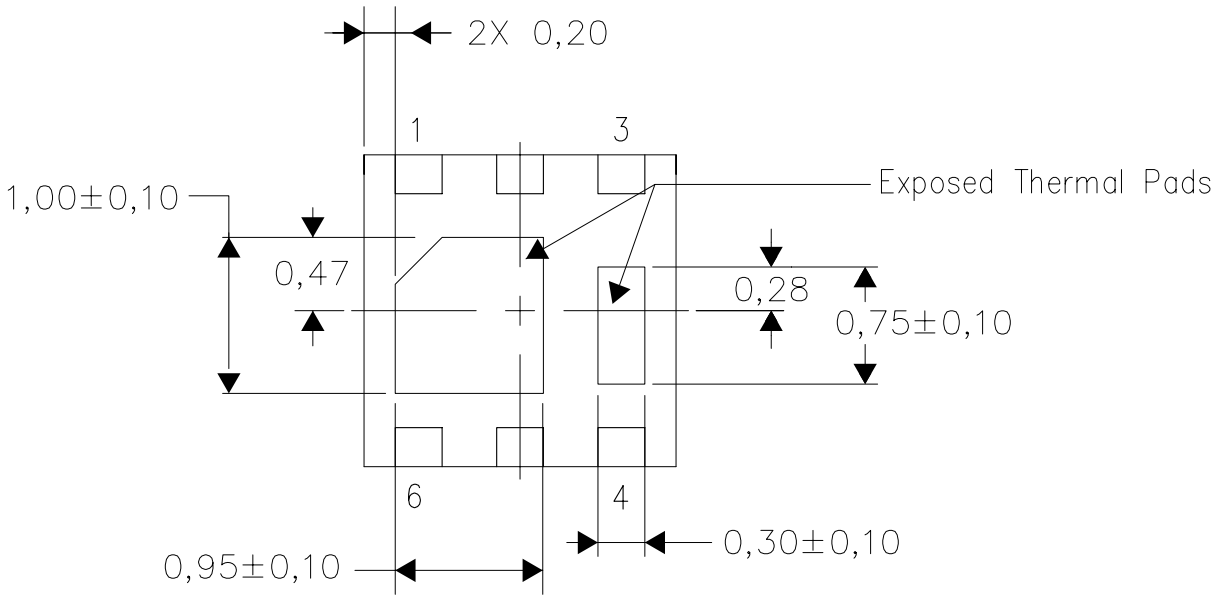
DQK (S–PWSON–N6)

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No–Lead (QFN) package and its advantages, refer to Application Report, Quad Flatpack No–Lead Logic Packages, Texas Instruments Literature No. SCBA017. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions

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